

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
S1	2	("20040113160").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/02 11:58
S2	220	(noboru near2 Oshima).in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/02 12:01
S4	7	S2 and (semiconductor near3 laser) and substrate and active and (protect\$4 or shad\$4 or insulat\$4).and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/02 12:08
S6	3002	thick\$4 and edge and (semiconductor near3 laser) and substrate and active and (protect\$4 or shad\$4 or insulat\$4) and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/02 12:09
S7	1407	(semiconductor near3 laser) and substrate and active and ((protect\$4 or shad\$4 or insulat\$4) with thick\$4 and edge) and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/02 12:10
S8	816	(semiconductor near3 laser) and substrate and active and ((protect\$4 or shad\$4 or insulat\$4) with thick\$4 and edge) and electrode and laminat\$3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/02 12:11
S11	1	(semiconductor near3 laser) and (substrate with laminat\$3 with active) and ((protect\$4 or shad\$4 or insulat\$4) with thick\$4) and edge and electrode and S2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/02 12:13
S9	91	(semiconductor near3 laser) and (substrate with laminat\$3 with active) and ((protect\$4 or shad\$4 or insulat\$4) with thick\$4) and edge and electrode	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/02 12:13
S12	1	("5625634").PN. OR ("6710375").URPN.	US-PGPUB; USPAT; USOCR	AND	ON	2005/12/02 12:15
S13	2	("4748482" "5625634").PN. OR ("6879620").URPN.	US-PGPUB; USPAT; USOCR	AND	ON	2005/12/02 12:16
S5	6	S4 and edge	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/02 12:23
S10	91	(semiconductor near3 laser) and (substrate with laminat\$3 with active) and ((protect\$4 or shad\$4 or insulat\$4) with thick\$4) and edge and electrode and S9	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/02 12:42

S15	79	(semiconductor near3 laser) and (substrate with laminat\$3 with active) and ((protect\$4 or shad\$4 or insulat\$4) with thick\$4) and edge and electrode and (light near3 emit\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/02 12:43
S16	52	(semiconductor near3 laser) and (substrate with laminat\$3 with active) and ((protect\$4 or shad\$4 or insulat\$4) with oxide) and edge and electrode and (light near3 emit\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/02 12:44
S18	3	(semiconductor near3 laser) and (substrate with laminat\$3 with active) and ((protect\$4 or shad\$4 or insulat\$4) with oxide) and edge and (electrode\$1 near3 gold) and (light near3 emit\$4) and (Si near3 (layer or region or film or medium))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/02 12:45
S19	8	("20030156614") or ("6,455,876") or ("6,618,409") or ("20050190807") or ("6,798,811") or ("6,893,887") or ("20020115303") or ("6,067,310").PN	US-PGPUB; USPAT	OR	OFF	2005/12/02 13:47
S14	16	("20030156614") or ("6,455,876") or ("6,618,409") or ("20050190807") or ("6,798,811") or ("6,893,887") or ("20020115303") or ("6,067,310").PN	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/12/02 13:47
S17	19	(semiconductor near3 laser) and (substrate with laminat\$3 with active) and ((protect\$4 or shad\$4 or insulat\$4) with oxide) and edge and electrode and (light near3 emit\$4) and (Si near3 (layer or region or film or medium))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/02 13:54
S20	30	(semiconductor near3 laser) and (substrate with laminat\$3 with active) and ((protect\$4 or shad\$4 or insulat\$4 or dielectric) with ((aluminum near2 oxide) or (Al"2"O"2") or titanium near2 oxide or (TiO"2") or (silicon near3 oxide) or (SiO"2") or oxide)) and edge and electrode and (light near3 emit\$4) and (Si near3 (layer or region or film or medium))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/02 13:59
S21	506	(semiconductor near3 laser) and (substrate and active) and ((protect\$4 or shad\$4 or insulat\$4 or dielectric) with ((aluminum near2 oxide) or (Al"2"O"2") or titanium near2 oxide or (TiO"2") or (silicon near3 oxide) or (SiO"2") or oxide)) and edge and electrode and (light near3 emit\$4) and (Si near3 (layer or region or film or medium))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/02 14:05
S22	99	(semiconductor near3 laser) and (substrate and active) and ((protect\$4 or shad\$4 or insulat\$4 or dielectric) with ((aluminum near2 oxide) or (Al"2"O"2") or titanium near2 oxide or (TiO"2") or (silicon near3 oxide) or (SiO"2") or oxide)) and edge and (electrode near4 (gold or Au)) and (light near3 emit\$4) and (Si near3 (layer or region or film or medium))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/06 11:02
S27	17	S25 and "372"/\$.ccls	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/06 11:23
S25	63	(semiconductor near3 laser) and substrate and active and ((aluminum near2 oxide) or (Al"2"O"2") or titanium near2 oxide or (TiO"2") or (silicon near3 oxide) or (SiO"2") or oxide) and (electrode near4 (gold or Au)) and (Si near1 (layer or region or film or medium)) and (thin near3 (film or region or layer or medium))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/06 11:23
S24	88	(semiconductor near3 laser) and substrate and active and ((aluminum near2 oxide) or (Al"2"O"2") or titanium near2 oxide or (TiO"2") or (silicon near3 oxide) or (SiO"2") or oxide) and (electrode near4 (gold or Au)) and (Si near2 (layer or region or film or medium)) and (thin near3 (film or region or layer or medium))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/06 11:43

S29	13	S28 and "372"/\$.ccls.	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/06 11:44
S26	28	S23 and "372"/\$.ccls.	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/06 11:44
S30	48	(semiconductor near3 laser) and substrate and active and ((aluminum near2 oxide) or (Al"2"O"2") or (titanium near2 oxide) or (TiO"2") or (silicon near3 oxide) or (SiO"2") or oxide) and (electrode near2 (gold or Au)) and (Si near1 (layer or region or film or medium))	US-PPGPUB	AND	ON	2005/12/06 11:45
S32	1	("20030013280").PN; OR ("6647047").URPN..	US-PPGPUB; USPAT; USOCR	AND	ON	2005/12/06 11:48
S31	48	(semiconductor near3 laser) and substrate and active and ((aluminum adj2 oxide) or (Al"2"O"2") or (titanium adj2 oxide) or (TiO"2") or (silicon adj2 oxide) or (SiO"2") or oxide) and (electrode near2 (gold or Au)) and (Si near1 (layer or region or film or medium))	US-PPGPUB	AND	ON	2005/12/06 12:00
S28	47	(semiconductor near3 laser) and substrate and active and ((aluminum near2 oxide) or (Al"2"O"2") or (titanium near2 oxide) or (TiO"2") or (silicon near3 oxide) or (SiO"2") or oxide) and (electrode near2 (gold or Au)) and (Si near1 (layer or region or film or medium))	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/06 15:35
S33	46	(semiconductor near3 laser) and substrate and active and ((aluminum near2 oxide) or (Al"2"O"2") or (titanium near2 oxide) or (TiO"2") or (silicon near3 oxide) or (SiO"2") or oxide) and (electrode near2 (gold or Au)) and (Si near1 (layer or region or film or medium)) and thick\$4	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/06 16:14
S34	10	(semiconductor near3 laser) and substrate and active and ((aluminum near2 oxide) or (Al"2"O"2") or (titanium near2 oxide) or (TiO"2") or (silicon near3 oxide) or (SiO"2") or oxide) and (electrode near2 (gold or Au)) and (Si near1 (layer or region or film or medium)) and (electrode near3 thick\$4)	USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/06 16:15
S35	21	(semiconductor near3 laser) and substrate and active and ((aluminum near2 oxide) or (Al"2"O"2") or (Al near7 O) or (titanium near2 oxide) or (TiO"2") or (silicon near3 oxide) or (SiO"2") or oxide) and (electrode near2 (gold or Au)) and (Si near1 (layer or region or film or medium)) and (electrode near thick\$4)	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/06 16:27
S36	73	(semiconductor near3 laser) and substrate and active and ((aluminum near2 oxide) or (Al"2"O"2") or (Al near7 O) or (titanium near2 oxide) or (TiO"2") or (silicon near3 oxide) or (SiO"2") or oxide) and (electrode near2 (gold or Au)) and (Si near1 (layer or region or film or medium)) and (electrode with thick\$4)	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/06 16:28
S23	198	(semiconductor near3 laser) and substrate and active and ((aluminum near2 oxide) or (Al"2"O"2") or titanium near2 oxide or (TiO"2") or (silicon near3 oxide) or (SiO"2") or oxide) and (electrode near4 (gold or Au)) and (Si near2 (layer or region or film or medium)) and (thin near3 (film or region or layer or medium))	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/06 16:35
S37	180	(semiconductor near3 laser) and substrate and active and ((aluminum near2 oxide) or (Al"2"O"2") or titanium near2 oxide or (TiO"2") or (silicon near3 oxide) or (SiO"2") or oxide) and (electrode near4 (gold or Au)) and (Si near2 (layer or region or film or medium)) and ((silicon or Si) near2 (film or region or layer or medium)) and (electrode with thick\$4)	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/06 17:17
S38	51	(laser) and substrate and active and (electrode near4 (gold or Au)) and (((aluminum near2 oxide) or (Al"2"O"2") or titanium near2 oxide or (TiO"2") or (silicon near3 oxide) or (SiO"2")) with ((silicon or Si) near2 (film or region or layer or medium)) with (electrode with thick\$4))	US-PPGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 06:28

L1	478	(laser) and substrate and active and (electrode near4 (gold or Au)) and (((aluminum near2 oxide) or (Al with O) or (titanium near2 oxide) or (Ti with O) or (silicon near3 oxide) or (Si with O)) with ((silicon or Si) near2 (film or region or layer or medium)) or (insulat\$4 or protect\$4 or reflect\$4 or shad\$4)) with (electrode with thick\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 06:35
L2	478	(laser) and substrate and active and (electrode near4 (gold or Au)) and (((aluminum near2 oxide) or (titanium near2 oxide) or (silicon near3 oxide)) with ((silicon or Si) near2 (film or region or layer or medium)) or (insulat\$4 or protect\$4 or reflect\$4 or shad\$4)) with (electrode with thick\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 07:22
L4	3070	3 not 2	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 07:23
L3	3548	(laser) and substrate and active and (((aluminum near2 oxide) or (titanium near2 oxide) or (silicon near3 oxide)) with ((silicon or Si) near2 (film or region or layer or medium)) or (insulat\$4 or protect\$4 or reflect\$4 or shad\$4)) with (electrode with thick\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 07:30
L5	3548	(laser) and substrate and active and (((aluminum near2 oxide) or (titanium near2 oxide) or (silicon near3 oxide)) with ((silicon or Si) near2 (film or region or layer or medium)) or (insulat\$4 or protect\$4 or reflect\$4 or shad\$4) with thick\$4) with (electrode with thick\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 07:31
L6	203	(laser) and substrate and active and (((aluminum near2 oxide) or (titanium near2 oxide) or (silicon near3 oxide)) with ((silicon or Si) near2 (film or region or layer or medium)) or (insulat\$4 or protect\$4 or reflect\$4 or shad\$4) with thick\$4) with (electrode with thick\$4)) and "372"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 07:32
L8	181	(semiconductor near2 laser) and substrate and active and (((aluminum near2 oxide) or (titanium near2 oxide) or (silicon near3 oxide)) with ((silicon or Si) near2 (film or region or layer or medium)) or (insulat\$4 or protect\$4 or reflect\$4 or shad\$4) with thick\$4) with (electrode with thick\$4)) and "372"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 07:37
S3	0	S2 and (flores near3 ruiz).xa	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 08:33
L12	7	L11 and "372"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 08:33
L11	220	(noboru near2 Oshima).in	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 08:33
L10	212	(semiconductor near2 laser) and substrate and active and (((aluminum near2 oxide) or (titanium near2 oxide) or alumina or (silicon near3 oxide)) with ((silicon or Si) near2 (film or region or layer or medium)) or (insulat\$4 or protect\$4 or reflect\$4 or shad\$4) with thick\$4) same (electrode with thick\$4)) and "372"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 08:41

L13	4	11 and (((aluminum near2 oxide) or (titanium near2 oxide) or alumina or (silicon near3 oxide)) with ((silicon or Si) near2 (film or region or layer or medium)) or (insulat\$4 or protect\$4 or reflect\$4 or shad\$4) with thick\$4) same (electrode with thick\$4))	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 08:42
L14	220	(noboru.near2 Oshima).in	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 09:42
L16	319	(semiconductor near2 laser) and substrate and active and (((aluminum near2 oxide) or (titanium near2 oxide) or (silicon near3 oxide)) with ((silicon or Si) near2 (film or region or layer or medium)) or (insulat\$4 or protect\$4 or reflect\$4 or shad\$4) with thick\$4) same (electrode with thick\$4)) and "438"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 10:00
L9	212	(semiconductor near2 laser) and substrate and active and (((aluminum near2 oxide) or (titanium near2 oxide) or (silicon near3 oxide)) with ((silicon or Si) near2 (film or region or layer or medium)) or (insulat\$4 or protect\$4 or reflect\$4 or shad\$4) with thick\$4) same (electrode with thick\$4)) and "372"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 10:00
L15	531	(semiconductor near2 laser) and substrate and active and (((aluminum near2 oxide) or (titanium near2 oxide) or (silicon near3 oxide)) with ((silicon or Si) near2 (film or region or layer or medium)) or (insulat\$4 or protect\$4 or reflect\$4 or shad\$4) with thick\$4) same (electrode with thick\$4)) and "257"/\$.ccls.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	AND	ON	2005/12/07 10:06

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... on a light emitting end surface 51a of a laser chip 51 ... **Oshima, Noboru; Sakata, Masahiko; Yokota, Makoto** Sharp Kabushiki Kaisha; November 30, 2004 # 6826218. ...
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... Masaaki ; Akino , Noboru ; Isozaki , N.* ; Ito , Takao ; Inoue , Takashi ; Usui , Katsutomi ; Ebisawa , Noboru ; Oshima , K.* ; Ohara ... Pulsed laser deposition of ...
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... Yb:glass laser oscillation and ... Akino , Noboru ; Isozaki , N.* ; Ito , Takao ; Inoue , Takashi ; Usui , Katsutomi ; Ebisawa , Noboru ; Oshima , K.* ; Ohara
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Laser bar locking apparatus - Patent 6879620

Thus, decrease of a maximum optical output value is prevented, and reliability of the laser chips is increased. Inventors: **Oshima, Noboru** ...
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Technical Report of ISSP ジスク No.2034(1988)-No.2827(1994)

2212, Toshihito Osada, Ryuta Yagi, Seiichi Kagoshima, **Noboru Miura, Masashi Oshima, Gunji Saito**, High-Field Magnetotransport in an Organic Con- ductor ...
www.issp.u-tokyo.ac.jp/labs/tosyo/techrep/techlist8394.html - 101k - Dec 5, 2005 - [Cached](#) - [Similar pages](#)

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14, 2001, Cl. 359/201, METHOD AND APPARATUS FOR AN INTEGRATED LASER BEAM SCANNER,



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1. **Nonlinear optical properties of SiO₂ layers**
Yang, G.M.; Amjadi, H.; Sessler, G.M.;
Electrets, 1996. (ISE 9), 9th International Symposium on
25-30 Sept. 1996 Page(s):478 - 483
IEEE CNF
2. **Nonlinear optical properties of SiO₂ layers**
Sessler, G.M.; Amjadi, H.; Yang, G.M.;
Electrical Insulation and Dielectric Phenomena, 1996. IEEE 1996 Annual Report of the Conference on
Volume 1, 20-23 Oct. 1996 Page(s):270 - 273 vol.1
IEEE CNF
3. **An electrostatically excited 2D-micro-scanning-mirror with an in-plane configuration of the driving electrodes**
Schenk, H.; Durr, P.; Kunze, D.; Lakner, H.; Kuck, H.;
Micro Electro Mechanical Systems, 2000. MEMS 2000. The Thirteenth Annual International Conference on
23-27 Jan. 2000 Page(s):473 - 478
IEEE CNF

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